




APPROVED
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EXTERNAL ISSUE
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Prepared		Product Specifications AN7522		
Checked				
Approved				

Structure	Silicon Monolithic Bipolar IC
Appearance	FP12S Plastic Package (Power Type with Fin)
Application	Low Frequency Amplifier
Function	BTL 3.0W x 2ch Power Amplifier with Standby Function and Volume Function

A	Absolute Maximum Ratings				
No.	Item	Symbol	Ratings	Unit	Note
1	Storage Temperature	Tstg	-55 ~ +150	° C	1
2	Operating Ambient Temperature	Topr	-25 ~ +70	° C	1
3	Operating Ambient Pressure	Popr	$1.013 \times 10^5 \pm 0.61 \times 10^5$ (1.0± 0.6)	Pa (atm)	
4	Operating Constant Acceleration	Gopr	9 810 (1 000)	m/s ² (G)	
5	Operating Shock	Sopr	4 900 (500)	m/s ² (G)	
6	Supply Voltage	Vcc	14	V	2
7	Supply Current	Icc	2.0	A	
8	Power Dissipation	P _D	1.92	W	Ta=70°C

Operating Supply Voltage Range	Vcc	3.5V ~ 13.5V
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Note 1) The temperature of all items shall be Ta=25°C except storage temperature, operating ambient temperature.

Note 2) At no signal input.

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No	Item	Symbol	Test Cir-cuit	Conditions	Limits			Unit	Note
					min	typ	max		
1	Quiescent Circuit Current	I _{CQ}	1	V _{in} =0V, V _{ol} =0V	-	45	100	mA	
2	Standby Current	I _{STB}	1	V _{in} =0V, V _{ol} =0V	-	1	10	μA	
3	Output Noise Voltage	V _{NO}	1	R _g = 10kΩ, V _{ol} =0V	-	0.10	0.4	mV _{rms}	1
4	Voltage Gain	G _V	1	P _O = 0.5W, V _{ol} =1.25V	31	33	35	dB	
5	Total Harmonic Distortion	THD	1	P _O = 0.5W, V _{ol} =1.25V	-	0.10	0.5	%	
6	Maximum Power Output	P _O	1	THD=10%, V _{ol} =1.25V	2.4	3.0	-	W	
7	Ripple Rejection Ratio	RR	1	R _g = 10kΩ, V _{ol} =0V V _r =0.5V _{rms} , f _r = 120Hz	30	50	-	dB	1
8	Output Offset Voltage	V _{off}	1	R _g = 10kΩ, V _{ol} =0V	-250	0	250	mV	
9	Volume Attenuation Ratio	Att	1	P _O = 0.5W, V _{ol} =0V	70	85	-	dB	1
10	Channel Balance 1	CB 1	1	P _O = 0.5W, V _{ol} =1.25V	-1	0	1	dB	
11	Channel Balance 2	CB 2	1	P _O = 0.5W, V _{ol} =0.6V	-3	0	3	dB	
12	Middle Voltage Gain	G _{vm}	1	P _O = 0.5W, V _{ol} =0.6V	20.5	23.5	26.5	dB	
13	Channel Crosstalk	CT	1	P _O = 0.5W, V _{ol} =1.25V	40	55	-	dB	

Note 1) For this measurement, use the BPF = 15Hz ~ 30kHz (12dB/OCT).

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B Electrical Characteristics		(Unless otherwise specified, the ambient temperature is 25°C ± 2°C, Vcc=8.0V, frequency=1kHz and RL=8Ω.)							
No	Item	Symbol	Test Circuit	Conditions	Limits			Unit	Note
					min	typ	max		
1	Standby pin current	ISTB2	1	Vin=0V, VSTB=3V	-	-	25	μA	
2	Volume pin current	IVOL	1	Vin=0V, Vol=0V	-12	-	-	μA	

Note) The above characteristics are reference values determined for IC design, but not guaranteed values for shipping inspection. If problems were to occur, counter measures will be sincerely discussed.

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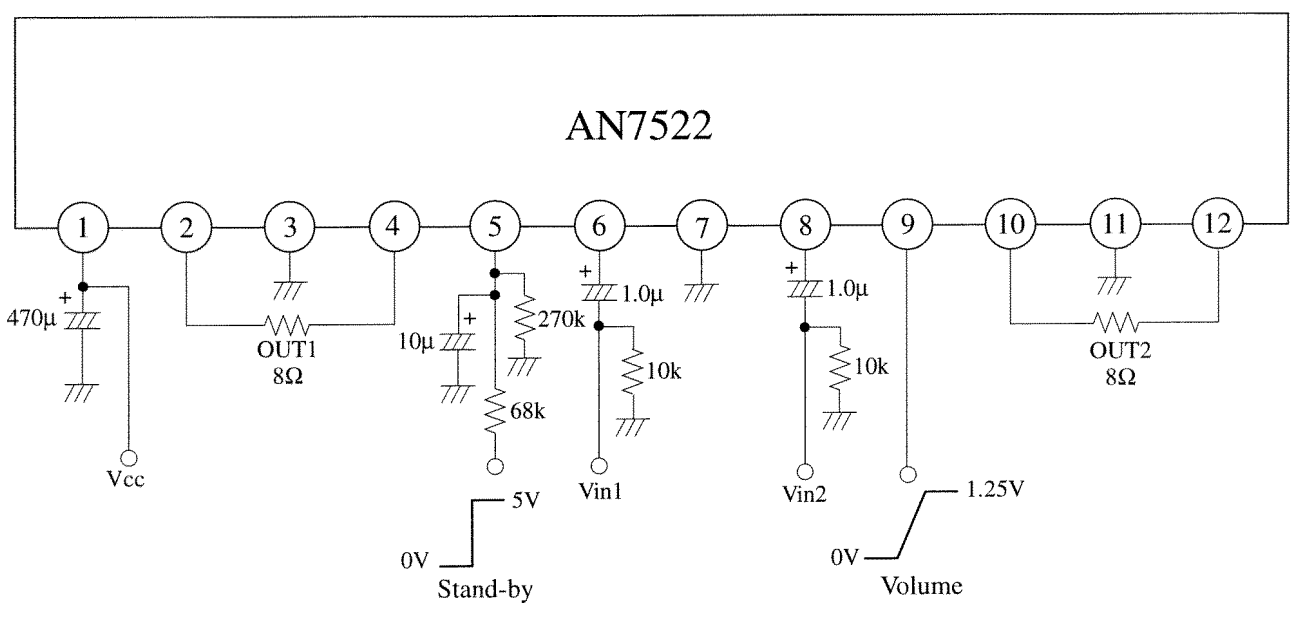
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(Description of test circuit and test method)

Test Circuit 1



Note) If the standby pin is open or 0V, the IC is on standby state.
 The IC is in the state of volume minimum if the Volume pin is ground.
 The IC is in the state of volume maximum if the Volume pin is open.

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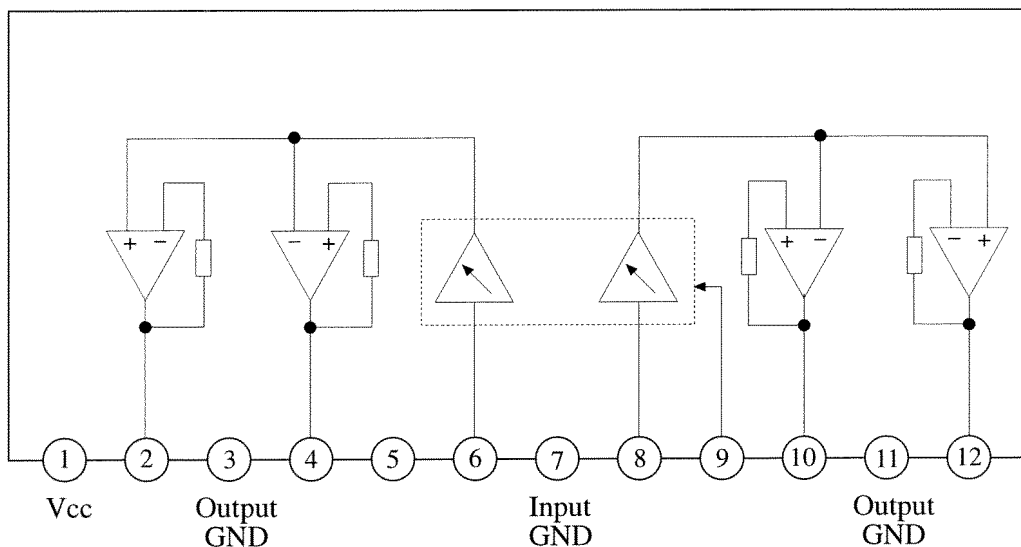
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Circuit Function Block Diagram



Pin Descriptions

Pin No.	Description	Pin No.	Description
1	Vcc	7	GND (Input)
2	Ch. 1 Output (+)	8	Ch.2 Input
3	GND (Ch. 1 Output)	9	Volume
4	Ch.1 Output (-)	10	Ch.2 Output (-)
5	Standby	11	GND (Ch.2 Output)
6	Ch.1 Input	12	Ch.2 Output (+)

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Checked	John Ng
Approved	S. Kasuga

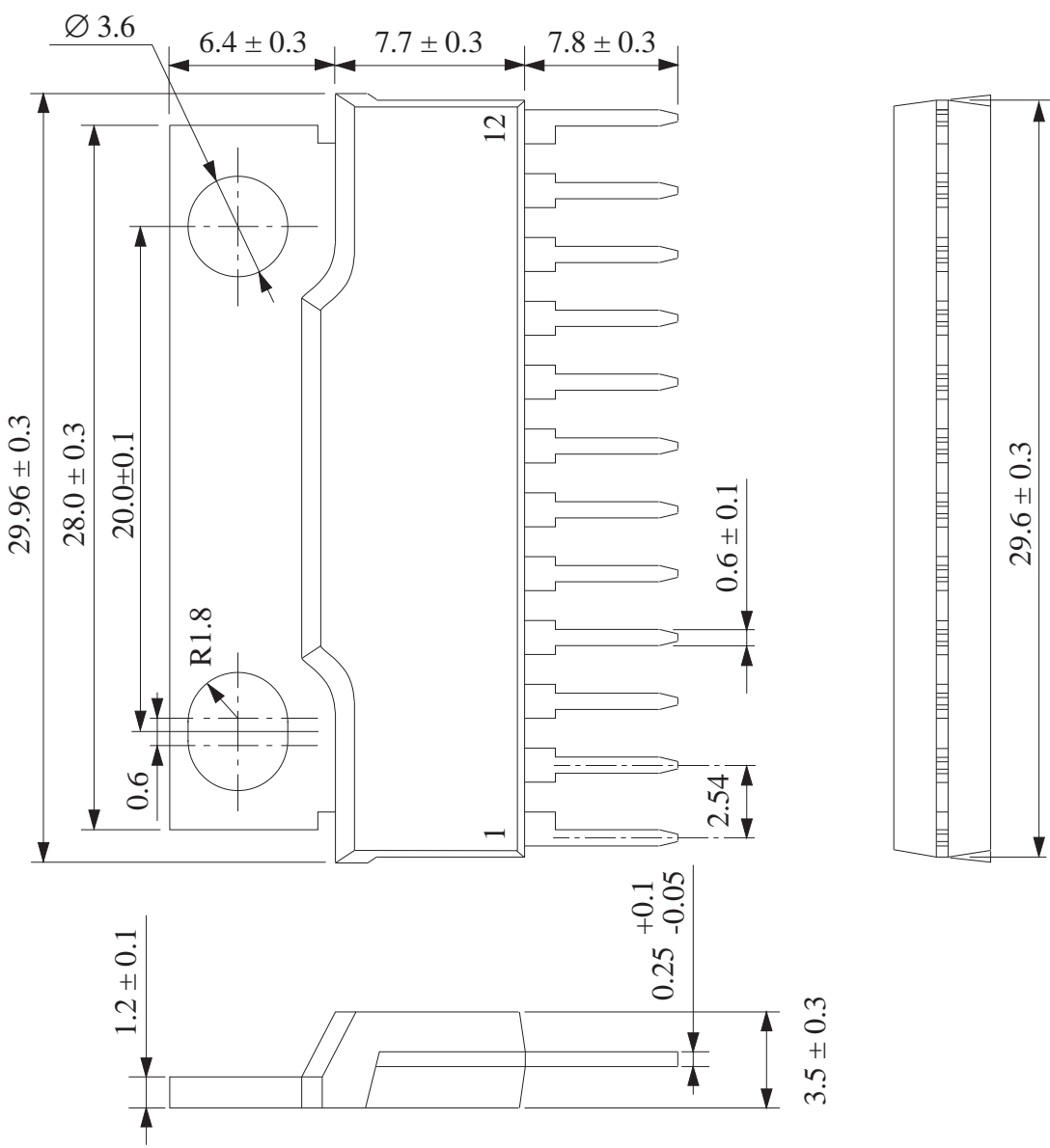
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Package Name	FP12S
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Unit : mm



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Prepared	Yiap Shi Hui	Product Specifications (Leadfree) AN7522	Ref No.	F
Checked	John Ng		Total Page	9
Approved	T. Sugimura		Page No.	7A

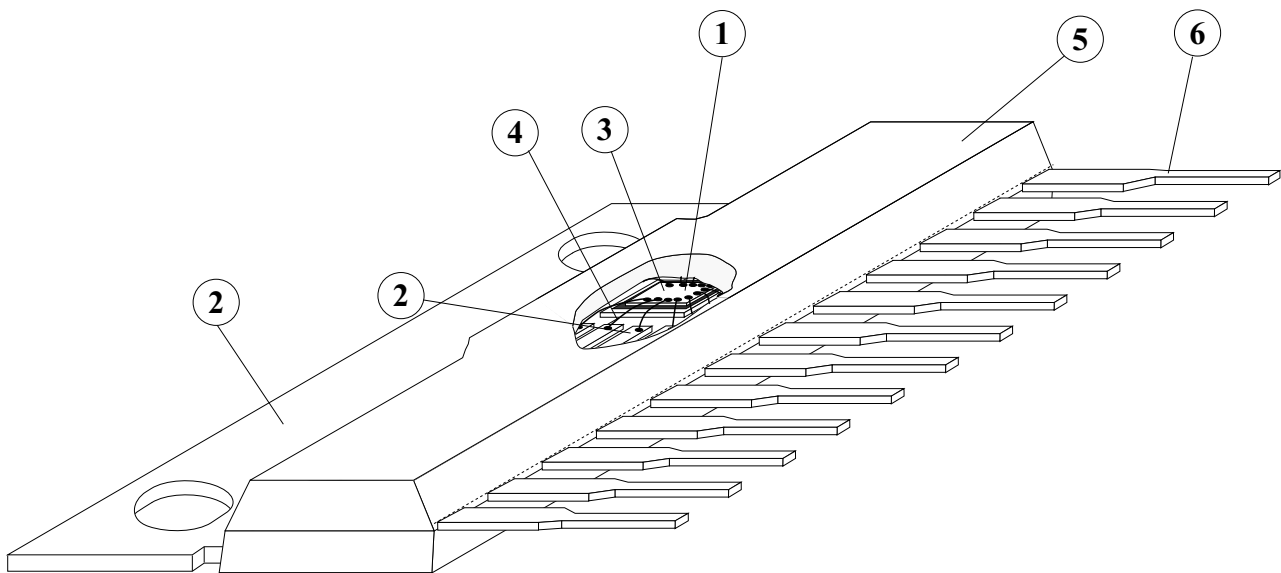
(Structure Description)

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Chip surface passivation	SiN, PSG , Others ()	①
Lead frame material	Fe group, Cu group , Others ()	②, ⑥
Inner lead surface process	Ag plating , Au plating, Others ()	②
Outer lead surface process	General Customer: Solder Plating (98Sn-2Bi) SC Buyback: Solder Dip (95.5Sn-2Ag-2Bi-0.5Cu)	⑥
Chip mounting method	Ag paste, Au-Si alloy, Solder (95.5Pb-2.5Ag-2Sn)** , Others ()	③
Wire bonding method	Thermalsonic bonding , Others ()	④
Wire material	Au , Diameter 38 μm, Others ()	④
Mold material	Epoxy , Others ()	⑤
Molding method	Transfer mold , Multiplunger mold, Others ()	⑤
Fin material	Cu group , Others ()	⑦

** Under RoHS exemption clause, Lead (Pb) in high melting temperature type solder (ie. tin-lead solder alloy containing more than 85% of lead), is exempted until 2010.

Package FP12S



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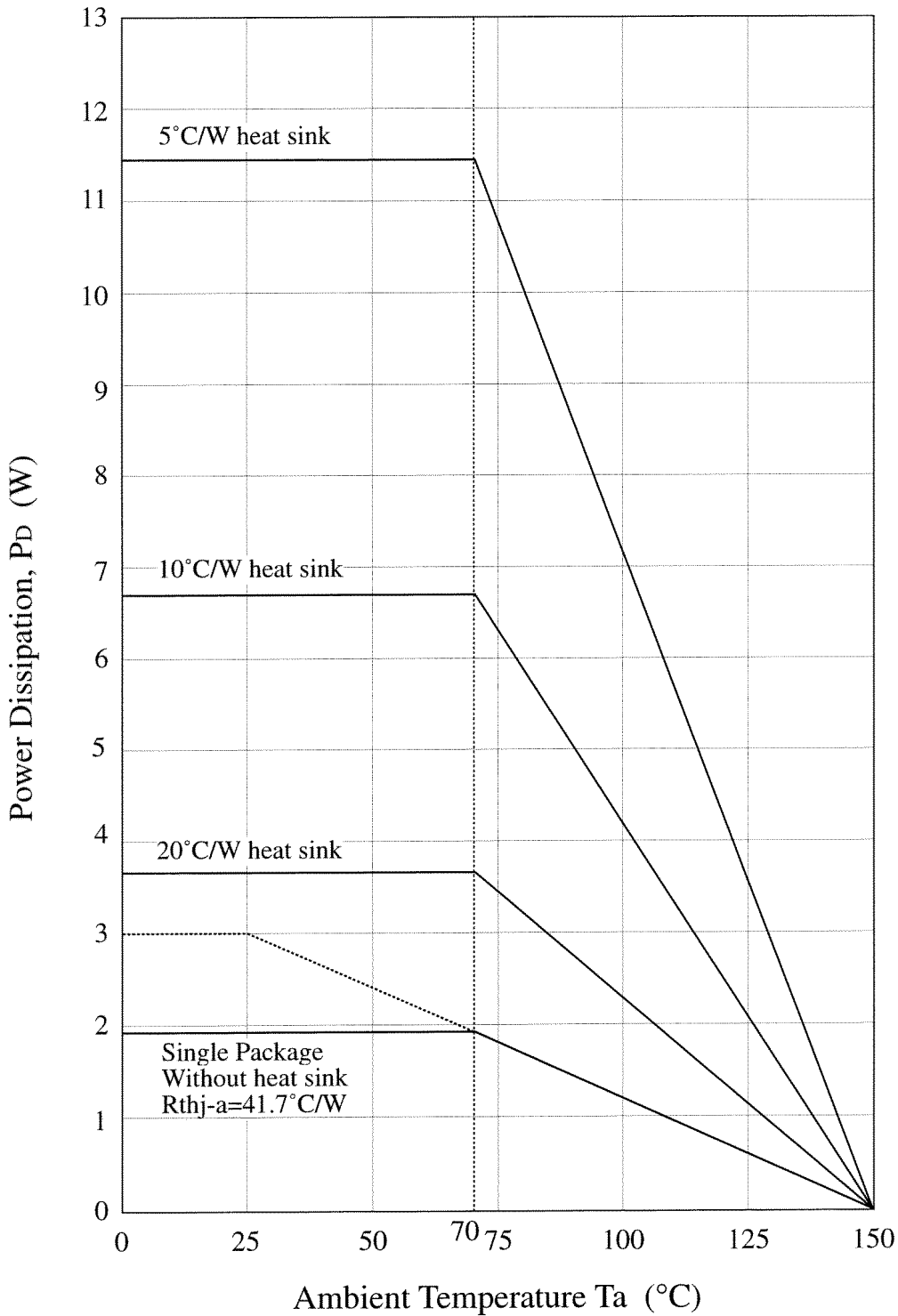
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Approved	<i>Shuang</i>

Product Specifications
(Technical Data)
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$$\begin{aligned} (R_{th(j-c)} &= 2^{\circ}\text{C/W}) \\ (R_{th(j-a)} &= 41.7^{\circ}\text{C/W}) \end{aligned}$$

FP-12S Package Power Dissipation
P_D - T_a



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(Precautions for use)

- 1) Make sure that the IC is free of any pin short-circuiting, ground fault, and load short-circuiting.
- 2) Ground the radiation fin so that there will be no difference in electric potential between the radiation fin and ground.
- 3) The thermal protection circuit operates at a Tj of approximately 150°C. The thermal protection circuit is reset automatically when the temperature drops.
- 4) Make sure that the heat radiation design is effective enough if the Vcc is comparatively high or the IC operates high output power.
- 5) Connect only ground pin for signal sources to the signal GND pin of the amplifier on the previous stage.
- 6) The electric surge voltage for this IC is low, therefore be extra careful when using the following pins (at 200pF):
 Pin 5 = +140V, Pin 6 = +140V, Pin 9 = +130V, Pin 8 = +150V

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